

L Number	Hits	Search Text	DB	Time stamp
1	7	("5741626"   "5814527"   "5905306"   "5952671"   "5998244"   "6091154"   "6111264").PN.	USPAT	2003/12/29 14:39
-	2016	(257/758).CCLS.	USPAT; US-PGPUB	2003/12/29 10:43
-	222	((257/758).CCLS.) and @pd>20030626	USPAT; US-PGPUB	2003/12/29 10:44
-	4	("6156648"   "6391785"   "6489233"   "6509266").PN.	USPAT	2003/12/29 10:57
-	7	("5952687"   "6228759"   "6239460"   "6358840"   "6387806"   "6399496"   "6420262"   "2002/0094673"   "2003/0015802").PN.	USPAT	2003/12/29 13:07
-	0	6649511.URPN.	USPAT	2003/12/29 13:08
-	2806	257/774	USPAT; US-PGPUB	2003/12/29 13:15
-	2472	257/774	USPAT	2003/12/29 13:16

	Document ID	Pages	Title	Current OR	Current XRef	Inventor
1	US 6407455 B1	13	Local interconnect using spacer-masked contact etch	257/774	257/775; 257/776; 257/E21.579; 257/E21.59	Wald, Phillip G. et al.
2	US 6380071 B1	15	Method of fabricating semiconductor device	438/634	257/760; 257/774; 438/622; 438/624; 438/633; 438/637; 438/672	Onuma, Takuji
3	US 6127734 A	56	Semiconductor device comprising a contact hole of varying width thru multiple insulating layers	257/774	257/306; 257/750; 257/775; 257/E21.577; 257/E21.579; 257/E21.648; 257/E21.654; 257/E23.019; 438/638; 438/639	Kimura, Hiroshi
4	US 5952724 A	15	Semiconductor device incorporating a stepped contact hole	257/774	257/904; 257/E23.019; 257/E23.145	Horiba, Shinichi
5	US 5894170 A	13	Wiring layer in semiconductor device	257/775	257/758; 257/774; 257/776; 257/E23.145; 257/E23.151	Ishikawa, Hiraku